

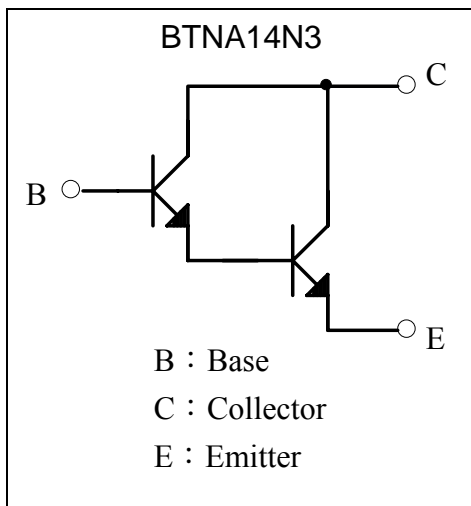
**General Purpose NPN Epitaxial Planar Transistor**

# BTNA14N3

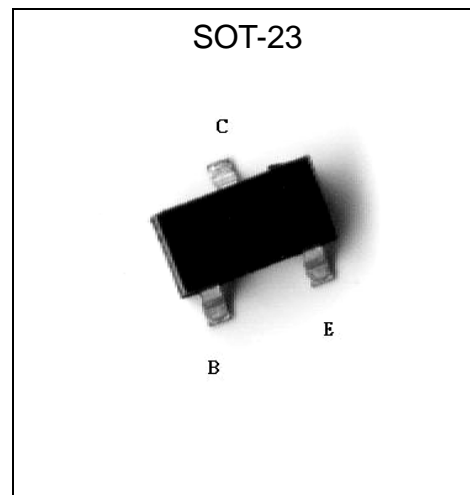
## Description

- The BTNA14N3 is a darlington amplifier transistor
- Complementary to BTPA64N3.
- Pb-free lead plating and halogen-free package

## Equivalent Circuit

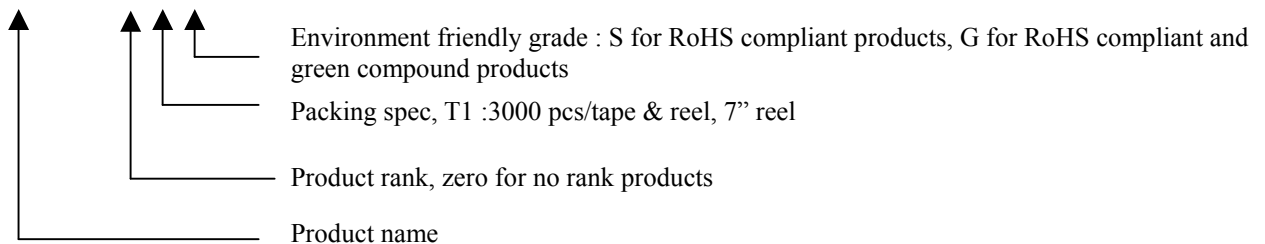


## Outline



## Ordering Information

Device	Package	Shipping
BTNA14N3-0-T1-G	SOT-23 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel



**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V <sub>CB0</sub>	100	V
Collector-Emitter Voltage	V <sub>CES</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	12	V
Collector Current	I <sub>C</sub>	0.5	A
Power Dissipation	P <sub>D</sub>	225	mW
Operating Junction Temperature Range	T <sub>j</sub>	-55~+150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~+150	°C

**Characteristics** (Ta=25°C)

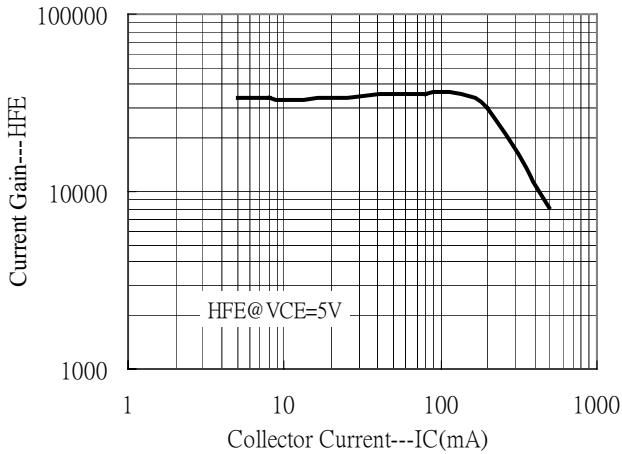
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CB0</sub>	100	-	-	V	I <sub>C</sub> =100μA
BV <sub>CES</sub>	60	-	-	V	I <sub>C</sub> =100μA, V <sub>BE</sub> =0V
BV <sub>CEO</sub>	60	-	-	V	I <sub>C</sub> =10mA
BV <sub>EBO</sub>	12	-	-	V	I <sub>C</sub> =10μA
I <sub>CB0</sub>	-	-	50	nA	V <sub>CE</sub> =80V
I <sub>EBO</sub>	-	-	50	nA	V <sub>EB</sub> =10V
*V <sub>CE(sat)</sub>	-	-	1.2	V	I <sub>C</sub> =100mA, I <sub>B</sub> =0.1mA
*V <sub>BE(on)</sub>	-	-	2.0	V	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA
*h <sub>FE1</sub>	10K	-	-		V <sub>CE</sub> =5V, I <sub>C</sub> =10mA
*h <sub>FE2</sub>	20K	-	-		V <sub>CE</sub> =5V, I <sub>C</sub> =100mA
f <sub>T</sub>	125	-	-	MHz	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=100MHz
C <sub>ob</sub>	-	-	7	pF	V <sub>CB</sub> =10V, f=1MHz

\*Pulse Test: Pulse Width ≤380μs, Duty Cycle≤2%

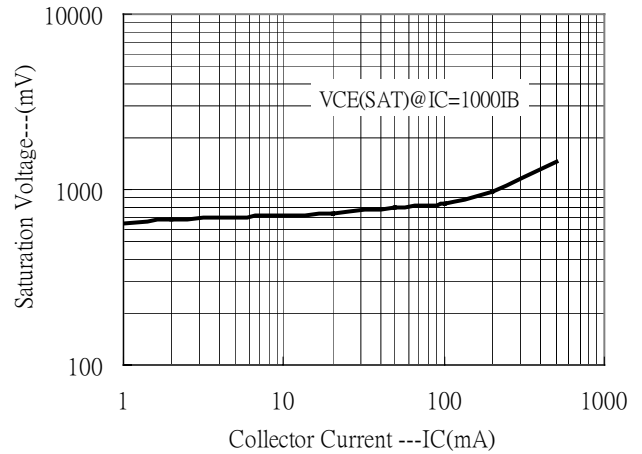


### Typical Characteristics

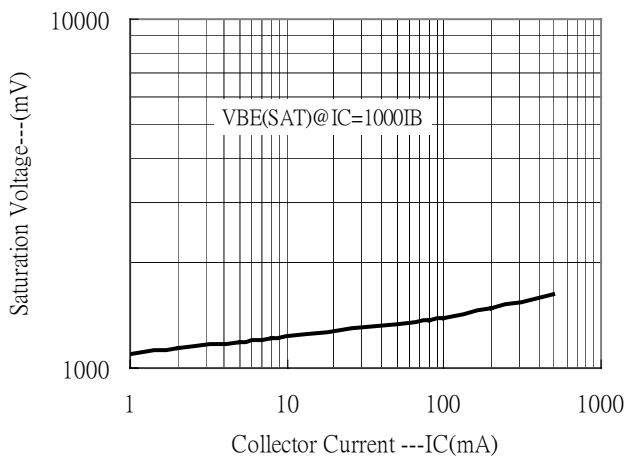
Current Gain vs Collector Current



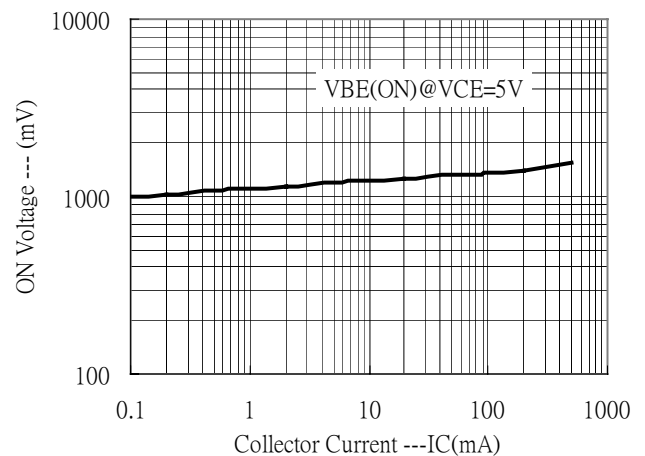
Saturation Voltage vs Collector Current



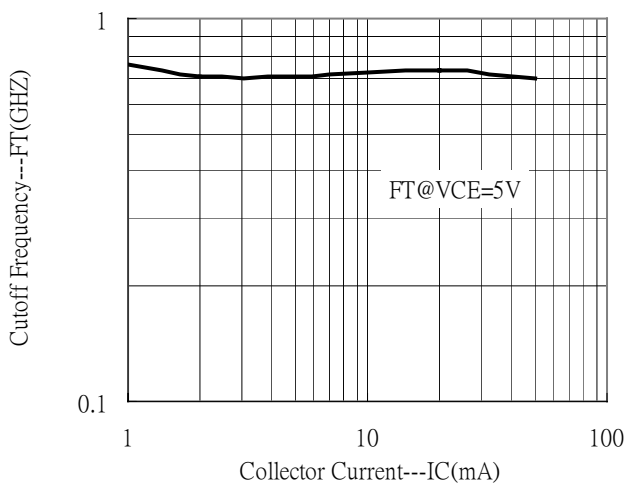
Saturation Voltage vs Collector Current



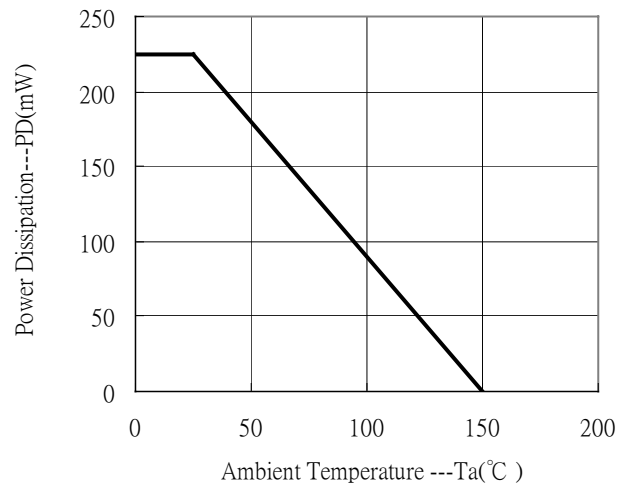
ON Voltage vs Collector Current



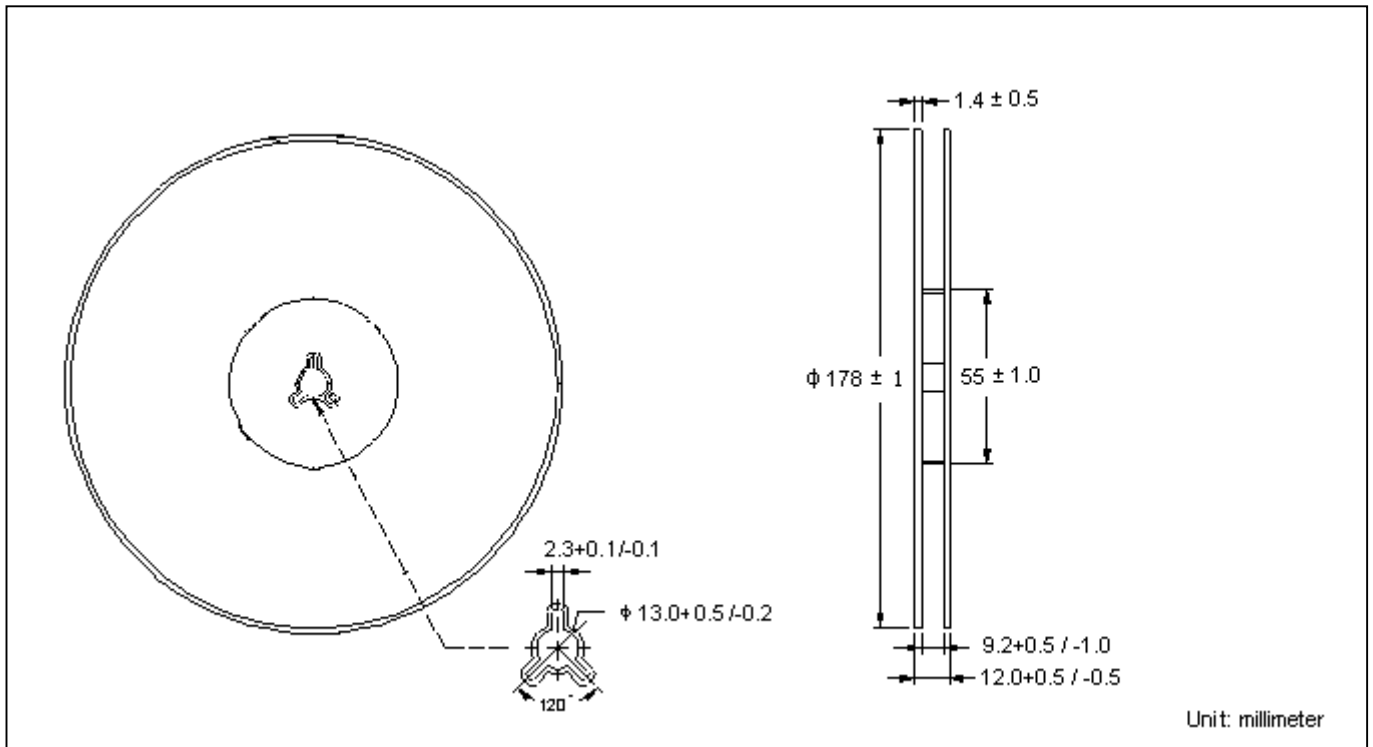
Cutoff Frequency vs Collector Current



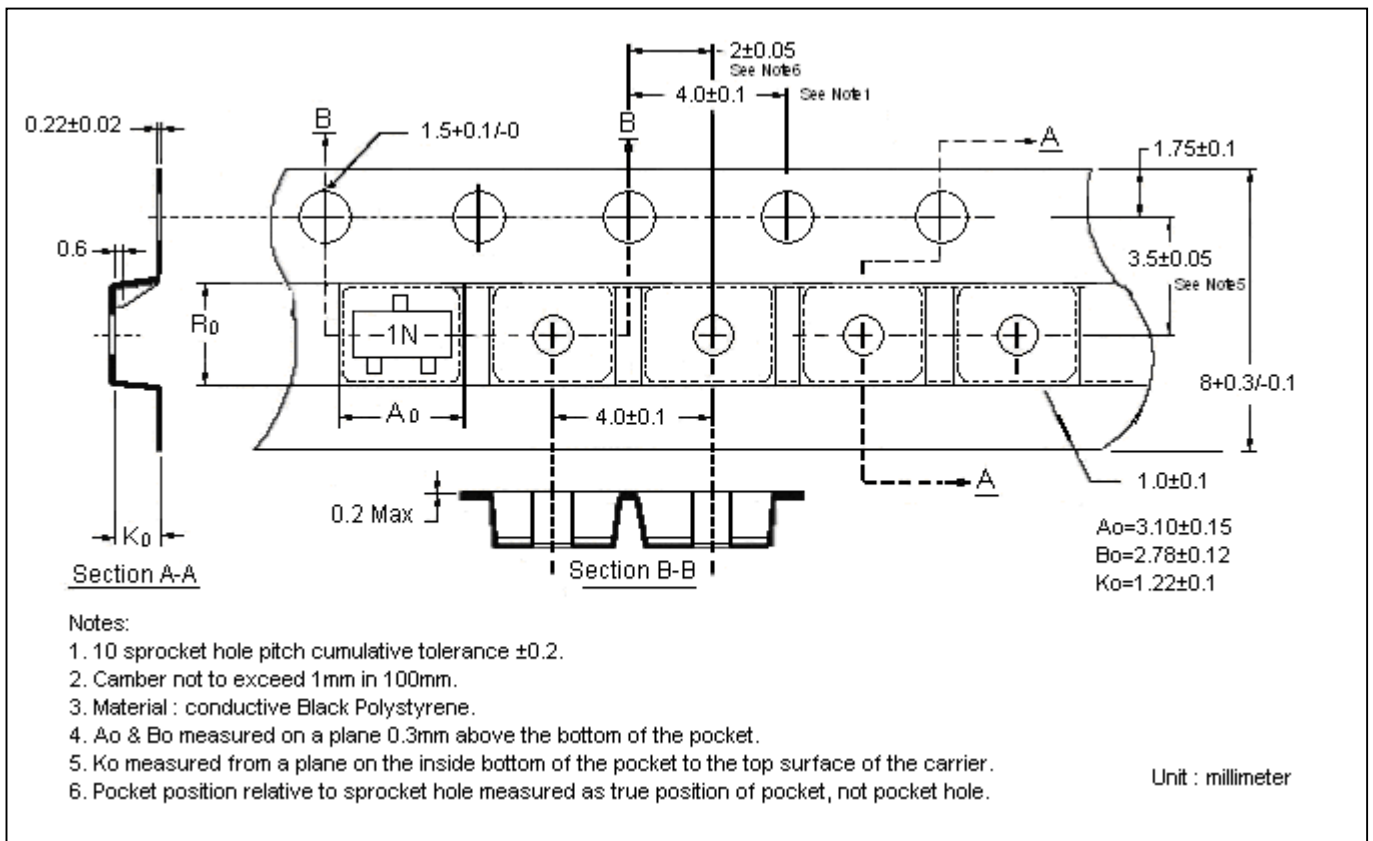
Power Derating Curve



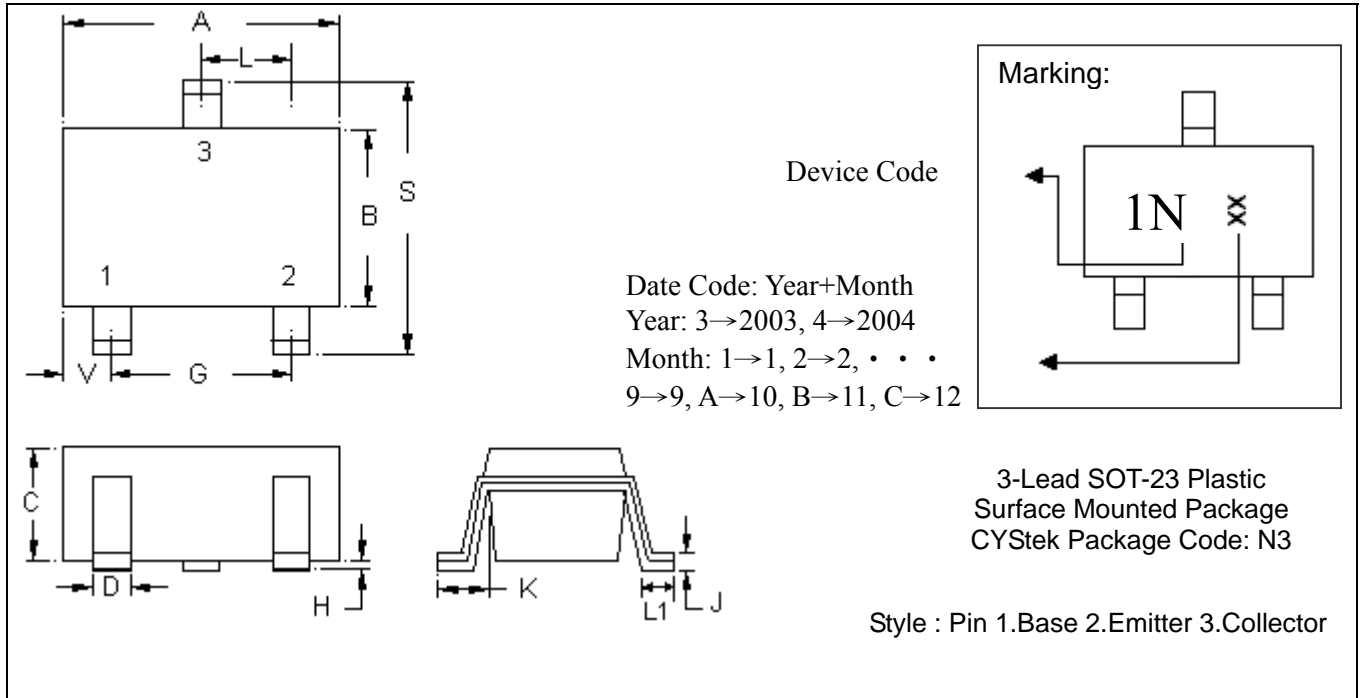
**Reel Dimension**



**Carrier Tape Dimension**



**SOT-23 Dimension**



\*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0032	0.0079	0.08	0.20
B	0.0472	0.0669	1.20	1.70	K	0.0118	0.0266	0.30	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1161	2.10	2.95
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0000	0.0040	0.00	0.10	L1	0.0118	0.0197	0.30	0.50

- Notes : 1.Controlling dimension : millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material :**

- Lead :Pure tin plated.
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0.

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